

2SC460, 2SC461

Silicon NPN Epitaxial Planar

REJ03G0682-0200
(Previous ADE-208-1046)
Rev.2.00
Aug.10.2005

Application

- 2SC460 high frequency amplifier, mixer
- 2SC461 VHF amplifier, mixer

Outline

RENESAS Package code: PRSS0003DA-C
(Package name: TO-92 (2))



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	2SC460	2SC461	Unit
Collector to base voltage	V_{CBO}	30	30	V
Collector to emitter voltage	V_{CEO}	30	30	V
Emitter to base voltage	V_{EBO}	5	5	V
Collector current	I_C	100	100	mA
Collector power dissipation	P_C	200	200	mW
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Electrical Characteristics

(Ta = 25°C)

Item	Symbol	2SC460			2SC461			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	—	—	30	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	—	—	30	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	—	—	0.5	μA	$V_{CB} = 18 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	—	—	0.5	μA	$V_{EB} = 2 \text{ V}, I_C = 0$
Base to emitter voltage	V_{BE}	—	0.63	0.75	—	0.63	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
DC current transfer ratio	h_{FE}^{*1}	100	—	200	35	—	200		$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	0.6	1.1	—	0.6	1.1	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Gain bandwidth product	f_T	—	230	—	—	230	—	MHz	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector output capacitance	C_{ob}	—	1.8	3.5	—	1.8	3.5	pF	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$
10.7 MHz power gain	PG	26	29	—	—	—	—	dB	$V_{CE} = 6 \text{ V}, I_E = -1 \text{ mA}$ $f = 10.7 \text{ MHz}$
100 MHz power gain	PG	—	—	—	13	17	—	dB	$V_{CE} = 6 \text{ V}, I_E = -1 \text{ mA}$ $f = 100 \text{ MHz}$
Noise figure	NF	—	2.0	—	—	—	—	dB	$V_{CE} = 6 \text{ V}, I_E = -1 \text{ mA}$ $f = 1 \text{ MHz}$ $R_g = 500 \Omega$

Note: 1. The 2SC461 is grouped by h_{FE} as follows.

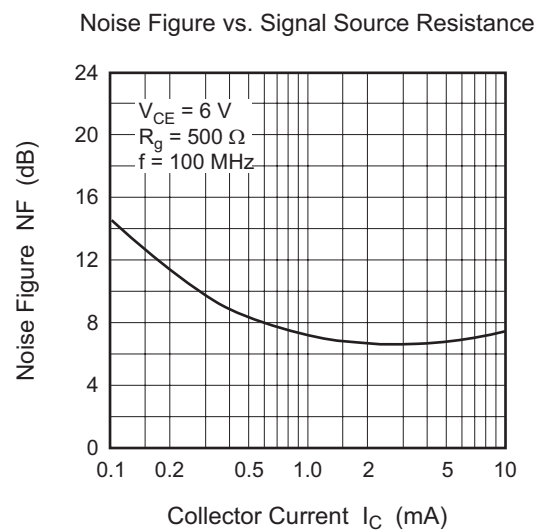
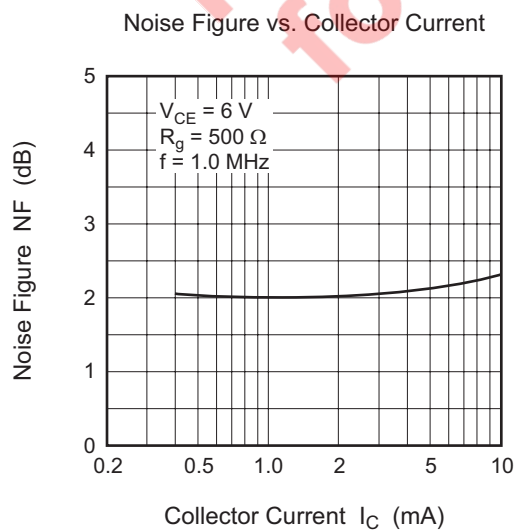
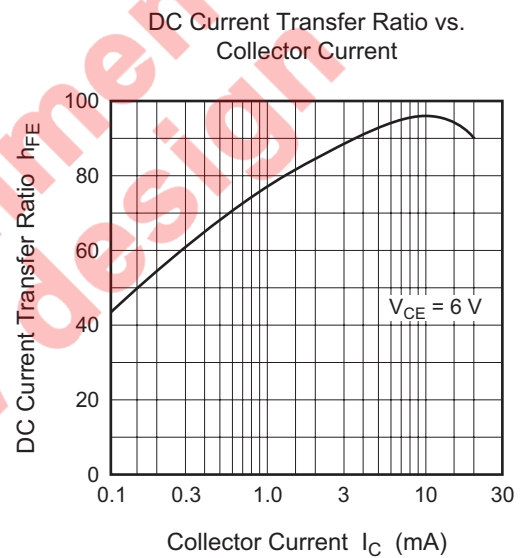
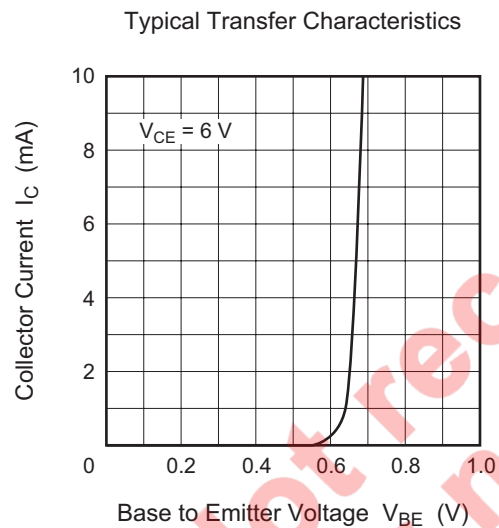
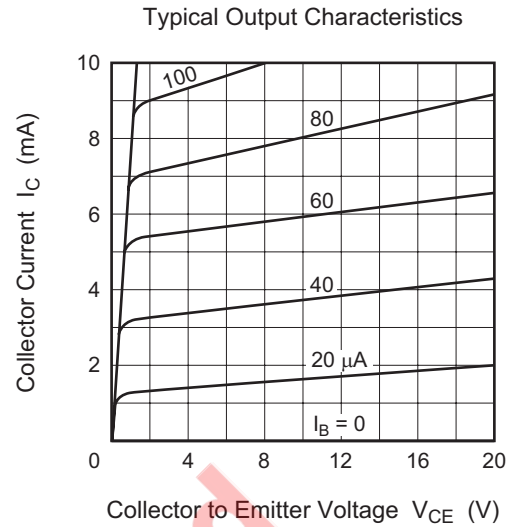
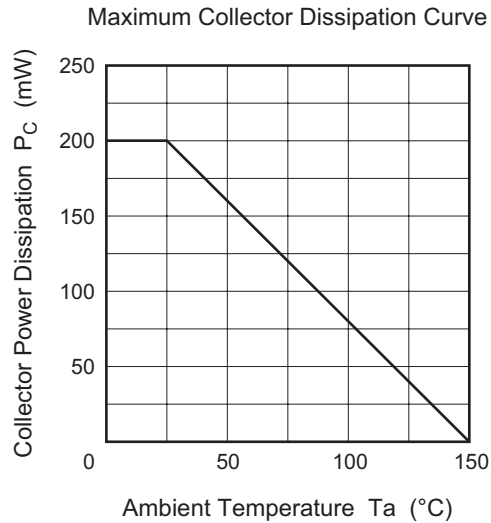
B	C
60 to 120	100 to 200

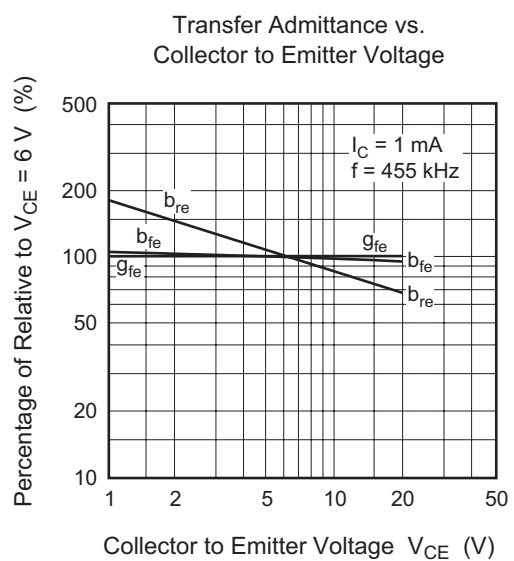
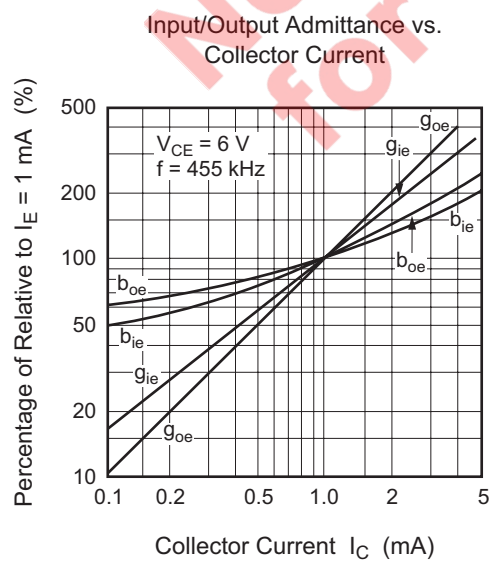
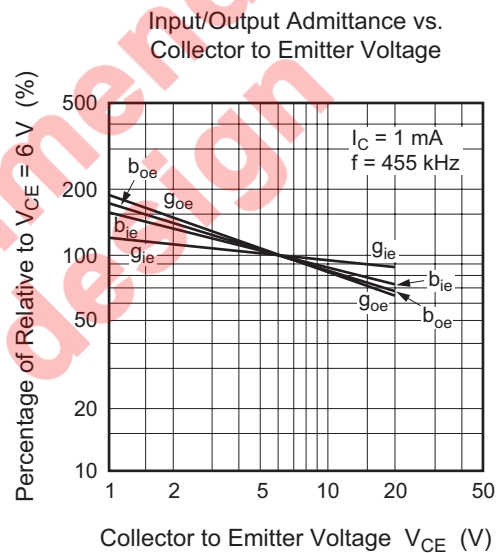
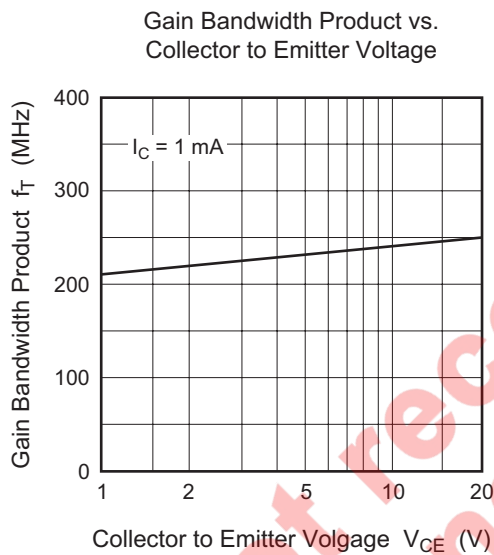
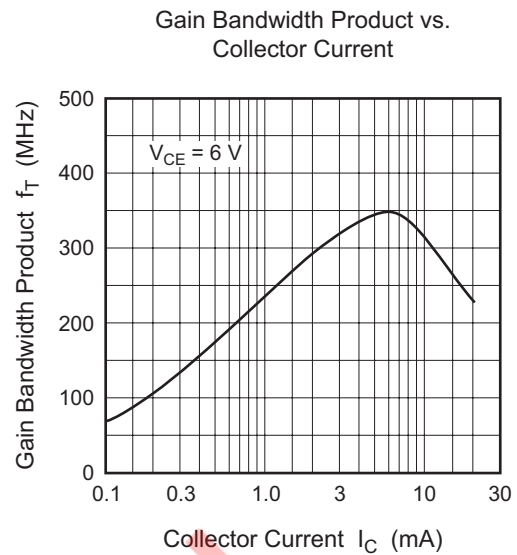
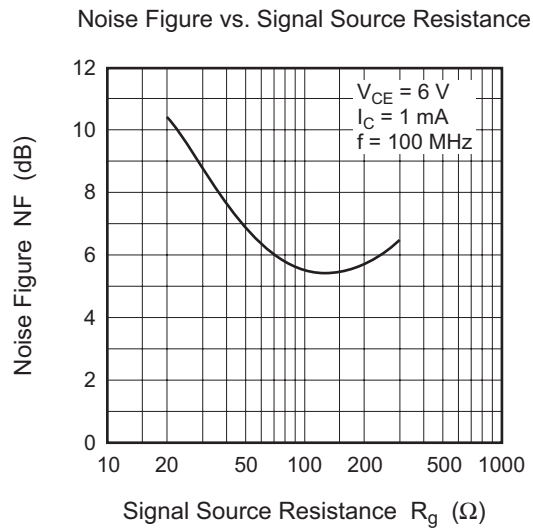
Small Signal y Parameters

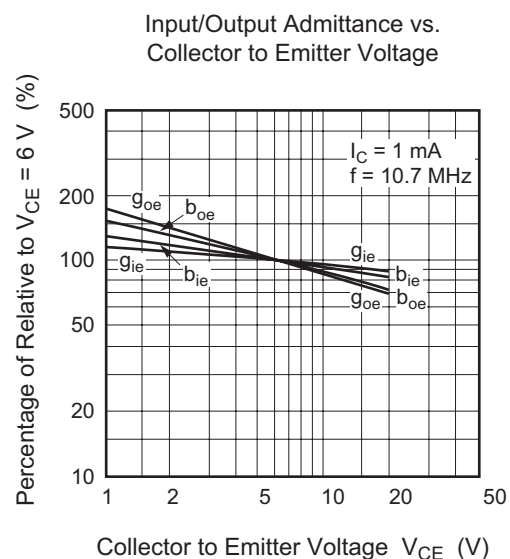
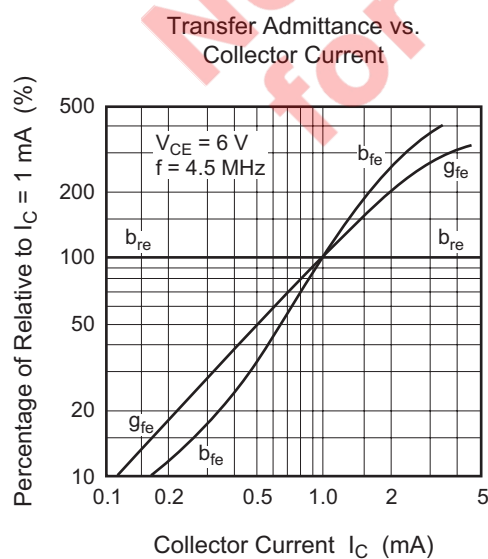
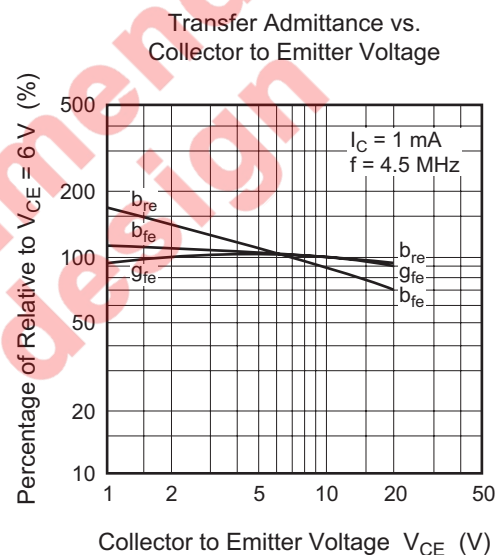
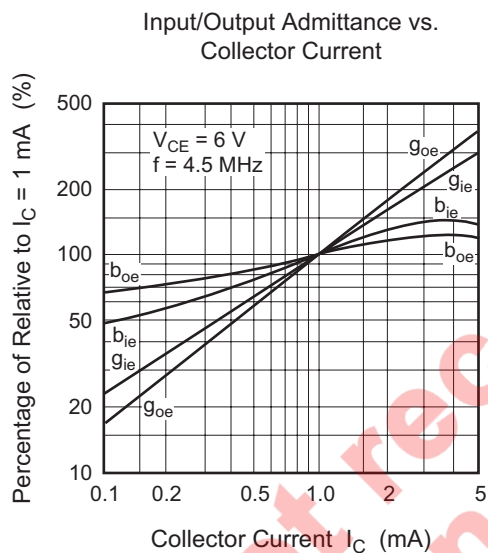
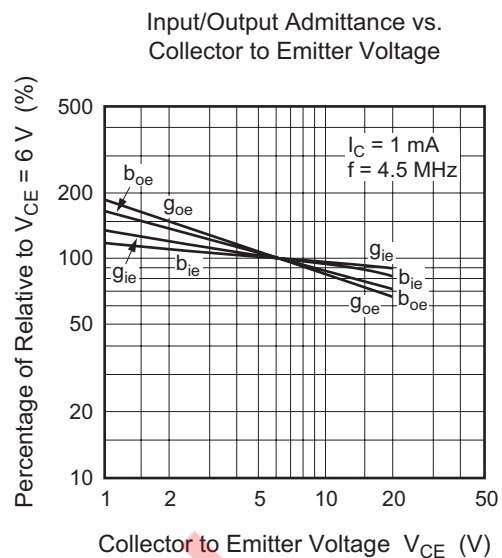
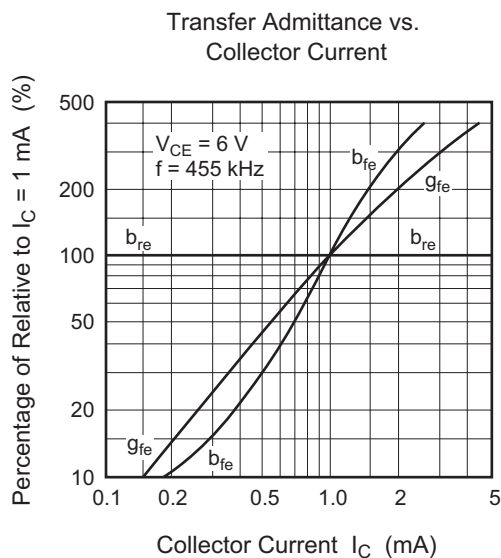
(V_{CE} = 6 V, I_C = 1 mA, Emitter Common)

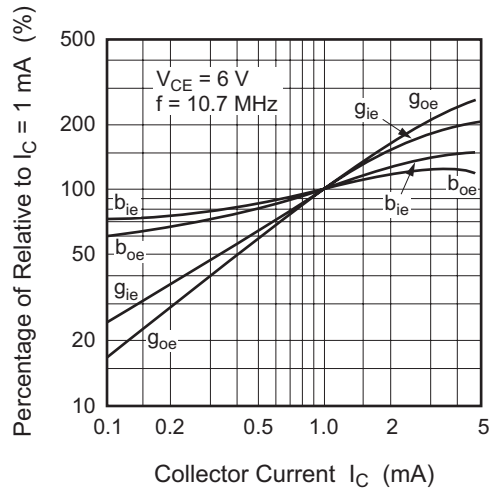
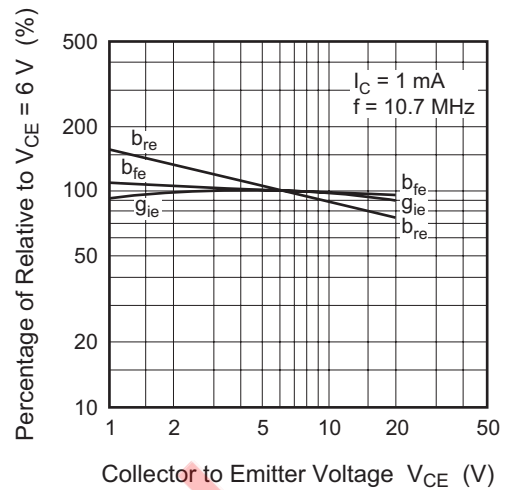
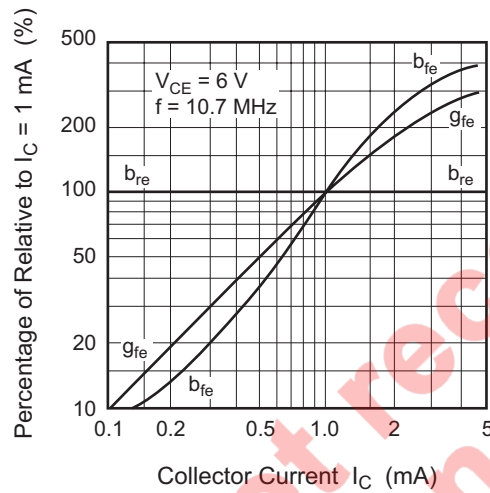
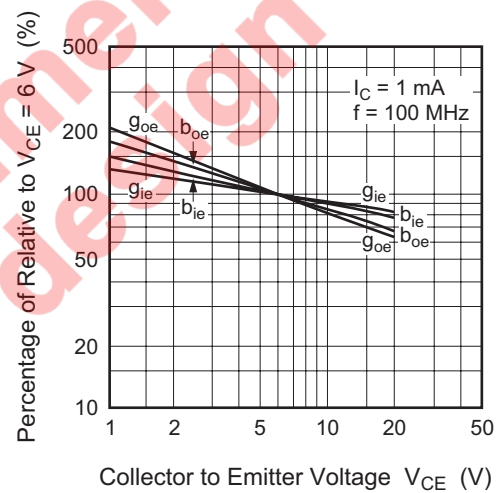
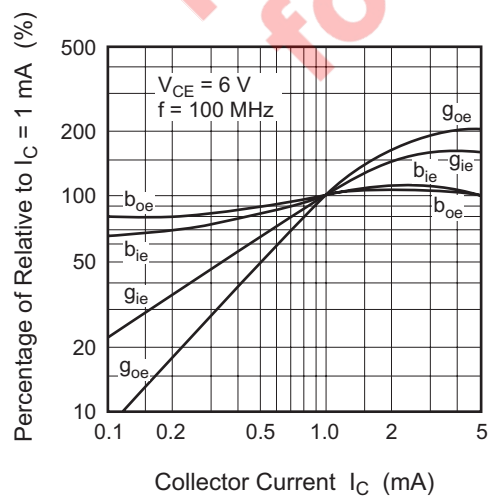
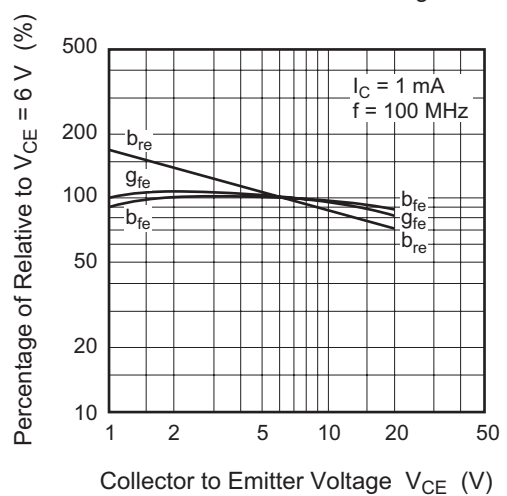
Item	Symbol	f	2SC460A, 2S461A	2SC460B, 2SC461B	2SC460C, 2SC461C	Unit
Input admittance	y _{ie}	455 kHz	0.58 + j0.074	0.42 + j0.068	0.30 + j0.051	mS
		4.5 MHz	0.65 + j0.79	0.50 + j0.7	0.35 + j0.57	
		10.7 MHz	0.91 + j2.0	0.61 + j1.9	0.39 + j1.3	
		100 MHz	7.4 + j14	5.6 + j12	3.8 + j6.0	
Reverse transfer admittance	y _{re}	455 kHz	-j0.003	-j0.003	-j0.003	mS
		4.5 MHz	-j0.04	-j0.04	-j0.04	
		10.7 MHz	-j0.13	-j0.13	-j0.13	
		100 MHz	-j1.0	-j1.0	-j1.0	
Forward transfer admittance	y _{fe}	455 kHz	38 - j0.1	37 - j0.1	37 - j0.2	mS
		4.5 MHz	35 - j1.0	35 - j1.2	34 - j1.8	
		10.7 MHz	34 - j2.5	34 - j2.5	33 - j4.5	
		100 MHz	28 - j20	28 - j19	20 - j19	
Output admittance	y _{oe}	455 kHz	0.0098 + j0.009	0.013 + j0.009	0.016 + j0.012	mS
		4.5 MHz	0.02 + j0.09	0.023 + j0.092	0.03 + j0.10	
		10.7 MHz	0.11 + j0.4	0.11 + j0.4	0.12 + j0.4	
		100 MHz	0.40 + j1.7	0.50 + j2.0	0.83 + j2.0	

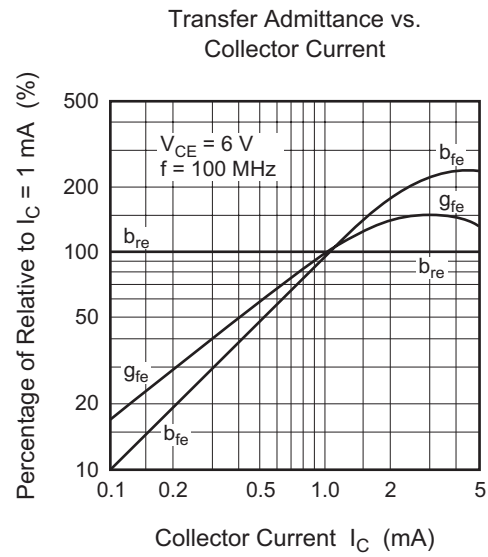
Main Characteristics







Input/Output Admittance vs.
Collector CurrentTransfer Admittance vs.
Collector to Emitter VoltageTransfer Admittance vs.
Collector CurrentInput/Output Admittance vs.
Collector to Emitter VoltageInput/Output Admittance vs.
Collector CurrentTransfer Admittance vs.
Collector to Emitter Voltage



Not recommended
for new design

Package Dimensions

JEITA Package Code	RENESAS Code	Package Name	MASS[Typ.]	Unit: mm
SC-43A	PRSS0003DA-C	TO-92(2) / TO-92(2)V	0.25g	

Ordering Information

Part Name	Quantity	Shipping Container
2SC460CTZ	2500	Hold Box, Radial Taping
2SC461BTZ		
2SC461CTZ		

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